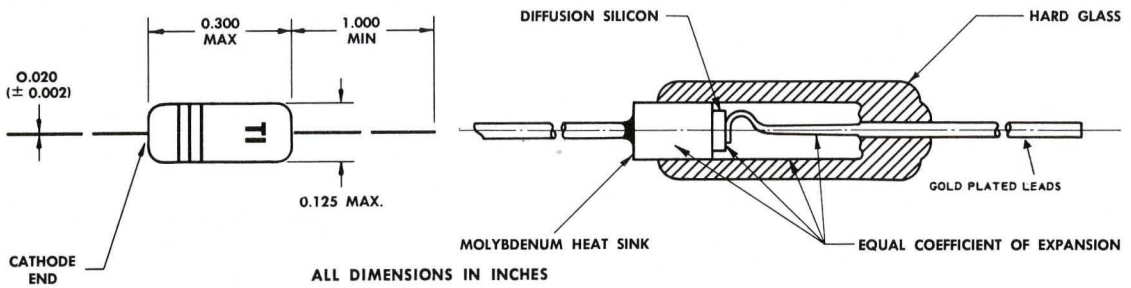
TYPES 1N643, 1N662 AND 1N663
DIFFUSED SILICON HIGH POWER COMPUTER DIODES

80 to 175 VOLTS PIV

Ruggedized to meet stringent military requirements
Designed for • fast recovery • higher conductance
• low capacitance

mechanical data

Hard glass hermetically sealed case with gold-to-gold contact. Unit weight is 0.195 gram.



maximum ratings

		1N643	1N662	1N663	
PIV	Peak Inverse Voltage at -65 to +150°C	175	80	80	v
I_O	Average Rectified Forward Current at +25°C	40	40	60	mA
I_O	Average Rectified Forward Current at +150°C	20	20	35	mA
i_I	Recurrent Peak Forward Current at +25°C	175	175	225	mA
T_A	Operating Temperature, Ambient	-65 to +150			°C
	Altitude	100,000			ft

specifications

V_Z	Saturation Voltage at 100 μa	200	100	100	V
LI_b	Maximum Reverse Current at 100v at +25°C	1	20 @ 50v	5 @ 75v	μA
LI_b	Maximum Reverse Current at 100v at +100°C	15	100 @ 50v	50 @ 75v	μA
E_b	Maximum Voltage Drop at I_O = 100 mA at 25°C	1		1	V
E_b	Maximum Voltage Drop at I_O = 10 mA at 25°C		1		V
t_{rr}	Maximum Reverse Recovery Time*	.3*	.5**	.5*	μsec
C	Typical Capacitance at -10v at 1 mc	2.7	2.7	2.7	μμfd

*Recovery time to 200K when switched from 5mA forward current to -40. Measurement made with a Hauman ND-1 standard pulse recovery test set approved by JETEC-14 and described in JAN-256.

**Recovery time to 100K when switched from 5mA forward current to -40. Measurement made with a Hauman ND-1 standard pulse recovery test set approved by JETEC-14 and described in JAN-256.

SEMICONDUCTOR-COMPONENTS DIVISION

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TEXAS INSTRUMENTS
INCORPORATED
SEMICONDUCTOR-COMPONENTS DIVISION
P. O. BOX 312 • 13500 N. CENTRAL EXPRESSWAY
DALLAS, TEXAS